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July 2014

Dual P-Channel PowerTrench® MOSFET

General Description

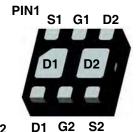
This device is designed specifically as a single package solution for the battery charge switch in cellular handset and other ultra-portable applications. It features two independent P-Channel MOSFETs with low on-state resistance for minimum conduction losses. When connected in the typical common source configuration, bi-directional current flow is possible.

The MicroFET 2x2 package offers exceptional thermal performance for it's physical size and is well suited to linear mode applications.

Features

- -3.0 A, -20V. $R_{DS(ON)} = 120 \text{ m}\Omega$ @ $V_{GS} = -4.5 \text{ V}$
 - $R_{DS(ON)}$ = 160 m Ω @ V_{GS} = -2.5 V
 - $R_{DS(ON)} = 240 \text{ m}\Omega$ @ $V_{GS} = -1.8 \text{ V}$
- Low Profile 0.8 mm maximun in the new package MicroFET 2x2 mm
- RoHS Compliant
- Free from halogenated compounds and antimony





G2

6 **D1** S1 5 **G2** G1 **D2** 3 4 **S2**

MicroFET 2X2

D1 Absolute Maximum Ratings T_A = 25°C unless otherwise noted

| Symbol | Parameter | | Ratings | Units |
|------------------|--|-----------|-------------|--------------------|
| V _{DSS} | MOSFET Drain-Source Voltage | | -20 | V |
| V _{GSS} | MOSFET Gate-Source Voltage | | ±8 | V |
| | Drain Current -Continuous | (Note 1a) | -3.0 | Α |
| ID | -Pulsed | | -6 | 7 ^ |
| | Power dissipation | (Note 1a) | 1.4 | |
| P _D | | (Note 1b) | 0.7 | \ \ _{\\\} |
| b | | (Note 1c) | 1.8 | ⊣ w |
| | | (Note 1d) | 0.8 | |
| T_J, T_{STG} | Operating and Storage Junction Temperature Range | | -55 to +150 | °C |

Thermal Characteristics

| $R_{\theta JA}$ | Thermal Resistance for Single Operation, Junction-to-Ambient | (Note 1a) | 86 | |
|-----------------|--|-----------|-----|-------|
| $R_{\theta JA}$ | Thermal Resistance for Single Operation, Junction-to-Ambient | (Note 1b) | 173 | °C/W |
| $R_{\theta JA}$ | Thermal Resistance for Dual Operation, Junction-to-Ambient | (Note 1c) | 69 | 10/00 |
| $R_{\theta JA}$ | Thermal Resistance for Dual Operation, Junction-to-Ambient | (Note 1d) | 151 | |

Package Marking and Ordering Information

| Device Marking | Device | Reel Size | Tape Width | Quantity |
|----------------|-----------|-----------|------------|------------|
| 027 | FDMA1027P | 7" | 8mm | 3000 units |

Electrical Characteristics $T_A = 25^{\circ}\text{C}$ unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Тур | Max | Units |
|--|---|--|-----|-----|------|-------|
| Off Chara | cteristics | | | | | |
| BV _{DSS} | Drain-Source Breakdown Voltage | $V_{GS} = 0V, I_D = -250\mu A$ | -20 | - | - | V |
| $\frac{\Delta BV_{DSS}}{\Delta T_{J}}$ | Breakdown Voltage Temperature Coefficient | $I_D = -250\mu A$, Referenced to 25°C | - | -12 | - | mV/°C |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} = -16V, V _{GS} = 0V | - | - | -1 | μА |
| I _{GSS} | Gate-Body Leakage, | $V_{GS} = \pm 8V$, $V_{DS} = 0V$ | - | - | ±100 | nA |

On Characteristics (Note 2)

| V _{GS(th)} | Gate Threshold Voltage | $V_{DS} = V_{GS}, I_{D} = -250 \mu A$ | -0.4 | -0.7 | -1.3 | V |
|--|---|---|------|------|------|-------|
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate Threshold Voltage Temperature Coefficient | $I_D = -250\mu A$, Referenced to 25°C | - | 2 | - | mV/°C |
| | $V_{GS} = -4.5V, I_D = -3.0A$ | - | 90 | 120 | | |
| | R _{DS(ON)} Static Drain-Source On-Resistance | $V_{GS} = -2.5V, I_D = -2.5A$ | - | 120 | 160 | |
| R _{DS(ON)} | | $V_{GS} = -1.8V, I_D = -1.0A$ | - | 172 | 240 | mΩ |
| | | $V_{GS} = -4.5V, I_D = -3.0A$ $T_J = 125^{\circ}C$ | - | 118 | 160 | |
| I _{D(on)} | On-State Drain Current | $V_{GS} = -4.5V, V_{DS} = -5V$ | -20 | - | - | Α |
| 9 _{FS} | Forward Transconductance | $V_{DS} = -5V, I_{D} = -3.0A$ | - | 7 | - | S |

Dynamic Characteristics

| C _{iss} | Input Capacitance | V 40V V 0V | - | 435 | - | pF |
|------------------|------------------------------|---|---|-----|---|----|
| C _{oss} | Output Capacitance | V _{DS} = -10V, V _{GS} = 0V, f = 1.0MHz | - | 80 | - | pF |
| C _{rss} | Reverse Transfer Capacitance | 1 - 1.500112 | - | 45 | - | pF |

Switching Characteristics (Note 2)

| t _{d(on)} | Turn-On Delay Time | | - | 9 | 18 | ns |
|---------------------|---------------------|---|---|-----|----|----|
| t _r | Turn-On Rise Time | V _{DD} = -10V, I _D = -1A | - | 11 | 19 | ns |
| t _{d(off)} | Turn-Off Delay Time | $V_{GS} = -4.5V$, $R_{GEN} = 6\Omega$ | - | 15 | 27 | ns |
| t _f | Turn-Off Fall Time | | - | 6 | 12 | ns |
| Q_g | Total Gate Charge | 101/ 1 004 | - | 4 | 6 | nC |
| Q_{gs} | Gate-Source Charge | $V_{DS} = -10V, I_{D} = -3.0A,$ $V_{GS} = -4.5V$ | - | 0.8 | - | nC |
| Q_{gd} | Gate-Drain Charge | VGS = -4.5V | - | 0.9 | - | nC |

Drain-Source Diode Characteristics and Maximum Ratings

| I _S | Maximum Continuous Drain-Source Diode Forward Current | | - | - | -1.1 | Α |
|-----------------|---|--|---|------|------|----|
| V_{SD} | Drain-Source Diode Forward Voltage | V _{GS} = 0V, I _S = -1.1 A (Note 2) | - | -0.8 | -1.2 | V |
| t _{rr} | Diode Reverse Recovery Time | I _F = -3.0A, dI _F /dt=100A/μs | - | 17 | - | ns |
| Q _{rr} | Diode Reverse Recovery Charge | IF= -3.0A, αΙΕ/αί=100A/μS | - | 6 | - | nC |

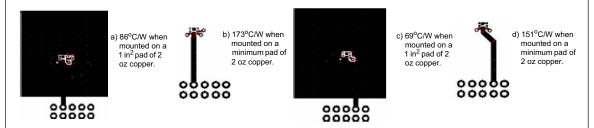
2

Electrical Characteristics $T_A = 25$ °C unless otherwise noted

- 1: R_{0JA} is determined with the device mounted on a 1 in² oz. copper pad on a 1.5 x 1.5 in. board of FR-4 material. R_{0JC}is guaranteed by design while R_{0JA} is determined by the user's board design.

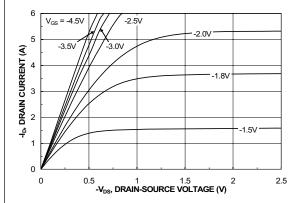
 (a) R_{0JA} = 86°C/W when mounted on a 1in² pad of 2 oz copper, 1.5" x 1.5" x 0.062" thick PCB. For single operation.

 - (b) $\rm R_{\theta JA}$ = 173°C/W when mounted on a minimum pad of 2 oz copper. For single operation.
 - (c) $R_{0JA} = 69^{\circ}$ C/W when mounted on a 1in² pad of 2 oz copper, 1.5" x 1.5" x 0.062" thick PCB, For dual operation, configured in parallel.
 - (d) $R_{\theta JA} = 151^{\circ}$ C/W when mounted on a minimum pad of 2 oz copper. For dual operation, configured in parallel.



2: Pulse Test : Pulse Width < 300us, Duty Cycle < 2.0%

Typical Characteristics



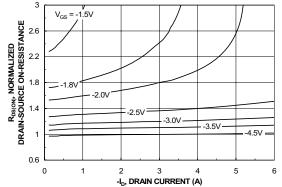
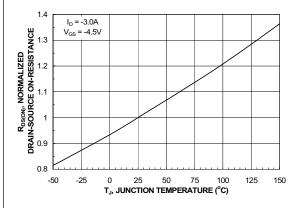


Figure 1. On-Region Characteristics

Figure 2. On-Resistance Variation with Drain Current and Gate Voltage



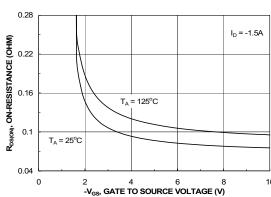
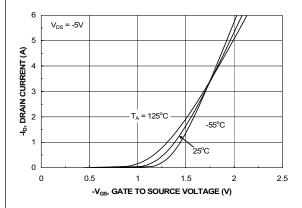


Figure 3. On-Resistance Variation with Temperature

Figure 4. On-Resistance Variation with Gate-to-Source Voltage



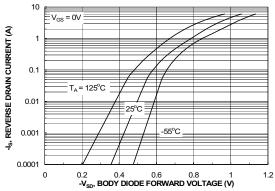
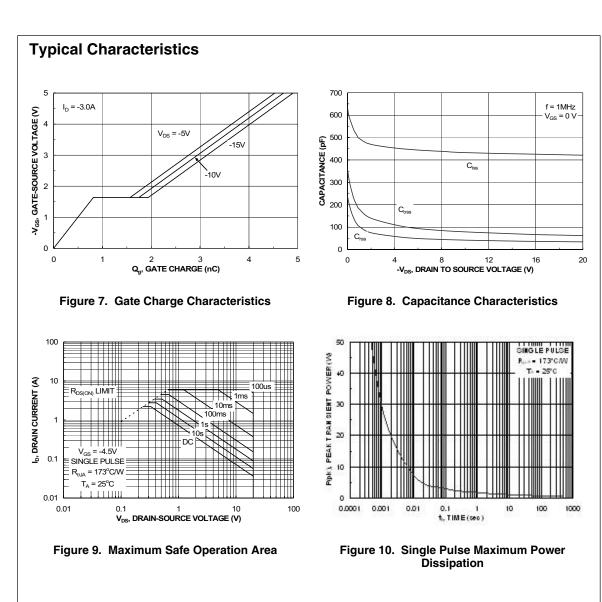


Figure 5. Transfer Characteristics

Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature



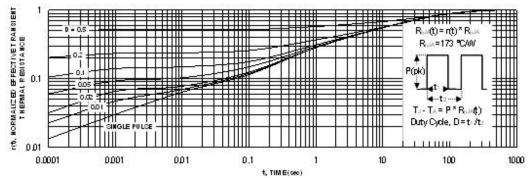
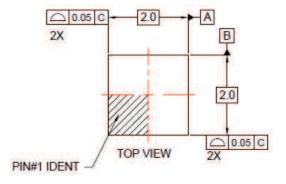
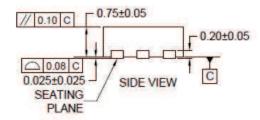


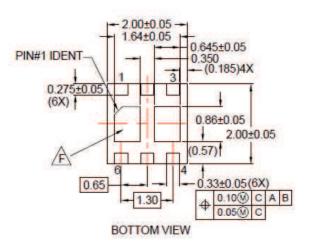
Figure 11. Transient Thermal Response Curve

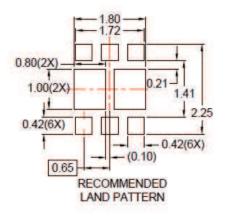
Thermal characterization performed using the conditions described in Note 1b. Transient thermal response will change depending on the circuit board design.

Dimensional Outline and Pad Layout









NOTES:

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- B. DIMENSIONS ARE IN MILLIMETERS.
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